

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	442	228/8.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:02
L3	466	228/9.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:13
L4	631	228/102.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:13
L5	1270	228/180.22.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:22
L6	224	228/231.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:22

EAST Search History

L7	271	228/232.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:23
L8	324	228/220.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:23
L9	3320	2 or 3 or 4 or 5 or 6 or 7 or 8	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:25
L11	497	((control\$4 near5 program)near5 (((pre or preliminary or post or final or subsequent) near5 heat\$3) or preheat\$3 or (pre adj heat\$3)or (post adj heat\$3) or anneal\$3 or temperature)) and (bump or bump\$3 or solder\$3 or bond\$3) and (wafer or semiconductor or chip)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 12:42
L12	7	9 and 11	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 07:36

EAST Search History

L13	1681	438/108.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:03
L14	3561	438/106.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:03
L15	2761	438/612.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:03
L16	1589	438/613.ccls.	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:03
L17	8074	13 or 14 or 15 or 16	US-PGPU B; USPAT; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 08:04

EAST Search History

L26	504	25 and (bump or bump\$3 or solder\$3 or bond\$3) and (wafer or semiconductor or chip)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 09:38
L27	424	25 and ((bump or bump\$3 or solder\$3 or bond\$3) near5(wafer or semiconductor or chip))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 09:52
L28	686	((bump or bump\$3 or solder\$3 or bond\$3)near5(device or system or apparatus))near5 ((heat\$3 or temperature or cool\$3) near5 control\$4))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 09:55
L29	27	((bump or bump\$3)near5(device or system or apparatus))near5 ((heat\$3 or temperature or cool\$3) near5 control\$4))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 09:55
L30	4340	((control\$4 near5 program)near5 (((pre or preliminary or post or final or subsequent) near5 heat\$3) or preheat\$3 or (pre adj heat\$3)or (post adj heat\$3) or anneal\$3 or temperature))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:11

EAST Search History

L31	1348	(bump\$3 near5 (semiconductor adj wafer))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:12
L37	28901	((bump\$3 solder\$3 or bond\$3) near5 wafer)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:59
L38	24	37 and 30	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:15
L39	85451	((bump\$3 solder\$3 or bond\$3) near5 semiconductor)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:18
L40	233367	((bump\$3 solder\$3 or bond\$3) near5 (semiconductor or substrate))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:18

EAST Search History

L41	114	40 and 30	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 10:28
L46	117	((bump\$3 solder\$3 or bond\$3) near5 control\$4 near5 temperature near5 (drop\$4 or lower\$3 or sink\$3 or fall\$3))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 11:01
L49	30	48 and ((control\$4 near5 program)near5 (((pre or preliminary or post or final or subsequent) near5 heat\$3) or preheat\$3 or (pre adj heat\$3)or (post adj heat\$3) or anneal\$3 or temperature))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 11:14
L53	11	52 and preheat\$3	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 13:15
L54	655	((Bond\$3 or bump\$3) near5 (stage or platform or location or station or court or floor) near5 ((post adj heat\$3) or anneal\$3 or temperature))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 13:18

EAST Search History

L55	44	((Bond\$3 or bump\$3) near5 (stage or platform or location or station or court or floor) near5 ((post adj heat\$3) or anneal\$3))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 13:21
L56	12	((bump\$3 near5 wafer) near5 ((post adj heat\$3) or anneal\$3))	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2006/10/30 13:22